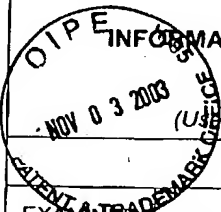


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Form PTO-1449 (MODIFIED)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 039153-0447 (G1152)	SERIAL NO. 10/016,439
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)		APPLICANT Lukanc et al.	
		FILING DATE 12/11/2001	GROUP ART UNIT 1756



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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
NB	A1	6,410,193	06/25/2002	Stivers et al.	430	5	
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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
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NB	A10	EP 0 708 367 B1	01/14/1998	EPO			X	

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Lukanc et al.

FILING DATE

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